

ABSTRACT OF THE DISCLOSURE

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A method of promoting crystalline performance of a region of irradiating laser beam by a plurality of times is provided.

5 A first crystalline region is formed by subjecting a portion of an amorphous semiconductor film to laser annealing by using laser beam having a wavelength in a range of 370 nm through 650 nm. It is preferable in carrying out laser annealing to irradiate laser beam after shaping the laser beam into linear beam having a shape at an irradiated face or a vicinity thereof in a linear shape by using an optical system. A second crystalline region is formed by subjecting a region including a portion of the first crystalline region to laser annealing. Crystalline performance of the first crystalline region formed as above, crystalline performance of the second crystalline region and crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same and a crystalline semiconductor film having excellent crystalline performance can be provided. When the
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20 crystalline semiconductor film constitutes an activation layer of TFT and electric properties of the TFT are measured, there are provided excellent properties having small dispersion.